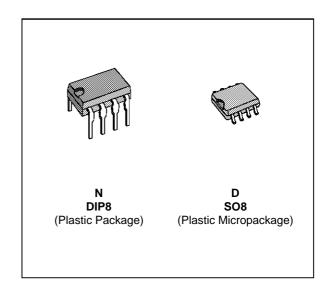


TL061 TL061A - TL061B

LOW POWER SINGLE J-FET OPERATIONAL AMPLIFIERS

- VERY LOW POWER CONSUMPTION:
- WIDE COMMON-MODE (UP TO V_{CC}⁺) AND DIFFERENTIAL VOLTAGE RANGES
- LOW INPUT BIAS AND OFFSET CURRENTS
- TYPICAL SUPPLY CURRENT: 200µA
- OUTPUT SHORT-CIRCUIT PROTECTION
- HIGH INPUT IMPEDANCE J-FET INPUT **STAGE**
- INTERNAL FREQUENCY COMPENSATION
- LATCH UP FREE OPERATION
- HIGH SLEW RATE: 3.5V/µs (TYP)



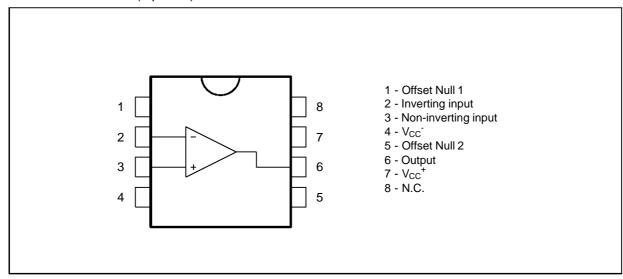
DESCRIPTION

The TL061, TL061A and TL061B are high speed J-FET input single operational amplifier family. Each of these J-FET input operational amplifiers incorporates well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.

ORDER CODES

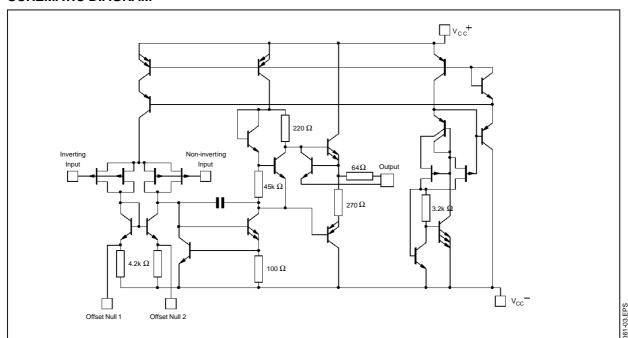
				_
Part Number	Temperature Range	Pac	kage	
Fait Number	Temperature Namye	N	D	1
TL061M/AM/BM	-55°C, +125°C	•	ı	
TL061I/AI/BI	-40°C, +105°C	•	ı	
TL061C/AC/BC	0°C, +70°C	•	•	Ē
Example: TL061	IN			7 2

PIN CONNECTIONS (top view)

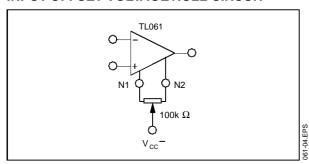


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SCHEMATIC DIAGRAM



INPUT OFFSET VOLTAGE NULL CIRCUIT



MAXIMUM RATINGS

Symbol	Parameter	TL061M,AM,BM	TL061I,AI,BI	TL061C,AC,BC	Unit
V_{CC}	Supply Voltage - (note 1)	±18	±18	±18	V
V_{i}	Input Voltage - (note 3)	±15	±15	±15	V
V _{id}	Differential Input Voltage - (note 2)	±30	±30	±30	V
P _{tot}	Power Dissipation	680	680	680	mW
	Output Short-Circuit Duration (Note 4)	Infinite	Infinite	Infinite	
T _{oper}	Operating Free-Air Temperature Range	-55 to +125	-40 to +105	0 to +70	°C
T _{stg}	Storage Temperature Range	- 65 to + 150	- 65 to + 150	- 65 to + 150	°C

Notes:

- All voltage values, except differential voltage, are with respect to the zero reference level (ground) of the supply voltages where the zero reference level is the midpoint between $V_{\rm CC}^+$ and $V_{\rm CC}^-$. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 volts, whichever is less. The output may be shorted to ground or to either supply. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

ELECTRICAL CHARACTERISTICS

 $V_{CC} = \pm 15V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Cumbal	Parameter	1	ΓL061N	1		TL061I T		TL0610	2	Unit	
Symbol	Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
V _{io}	$ \begin{array}{l} \text{Input Offset Voltage } (R_s = 50\Omega) \\ T_{amb} = 25^{^{0}}C \\ T_{min.} \leq T_{amb} \leq T_{max.} \end{array} $		3	6 9		3	6 9		3	15 20	mV
DV_io	Temperature Coefficient of Input Offset Voltage ($R_s = 50\Omega$)		10			10			10		μV/°C
l _{io}			5	100 20		5	100 10		5	200 5	pA nA
l _{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max}$.		30	200 50		30	200 20		30	400 10	pA nA
V _{icm}	Input Common Mode Voltage Range	±11.5	+15 -12		±11.5	+15 -12		±11	+15 -12		V
V _{OPP}		20 20	27		20 20	27		20 20	27		V
Avd	Large Signal Voltage Gain $(R_L = 10k\Omega, V_o = \pm 10V)$ $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max}$.	4 4	6		4 4	6		3 3	6		V/mV
GBP	Gain Bandwidth Product $(T_{amb} = 25^{\circ}C, R_{L} = 10k\Omega$ $C_{L} = 100pF)$		1			1			1		MHz
Ri	Input Resistance		10 ¹²			10 ¹²			10 ¹²		Ω
CMR	Common Mode Rejection Ratio $(R_s = 50\Omega)$	80	86		80	86		70	76		dB
SVR	Supply Voltage Rejection Ratio $(R_s = 50\Omega)$	80	95		80	95		70	95		dB
Icc	Supply Current (T _{amb} = 25°C, no load, no signal)		200	250		200	250		200	250	μΑ
P_D	Total Power Consumption (T _{amb} = 25°C, no load, no signal)		6	7.5		6	7.5		6	7.5	mW

^{*} The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

ELECTRICAL CHARACTERISTICS (continued)

 $V_{CC} = \pm 15V, T_{amb} = 25^{\circ}C$

Symbol	Parameter	Т	L061C,I,I	Unit	
Symbol	r ai ainetei	Min.	Тур.	Max.	
SR	Slew Rate ($V_i = 10V$, $R_L = 10k\Omega$, $C_L = 100pF$, $A_V = 1$)	1.5	3.5		V/μs
t _r	Rise Time ($V_i = 20$ mV, $R_L = 10$ k Ω , $C_L = 100$ pF, $A_V = 1$)		0.2		μs
Kov	Overshoot Factor (V_i = 20mV, R_L = 10k Ω , C_L = 100pF, A_V = 1) (see figure 1)		10		%
e _n	Equivalent Input Noise Voltage $(R_s = 100\Omega, f = 1KHz)$		42		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

ELECTRICAL CHARACTERISTICS (continued)

 $V_{CC} = \pm 15V$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

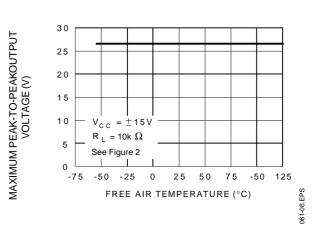
Symbol	Parameter	TL06	1AC,A	I,AM	TL06	1BC,B	I,BM	Unit
Symbol	rarameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Offic
V _{io}	Input Offset Voltage ($R_s = 50\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$		3	6 7.5		2	3 5	mV
DV_io	Temperature Coefficient of Input Offset Voltage ($R_s = 50\Omega$)		10			10		μV/°C
I _{io}	Input Offset Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \leq T_{amb} \leq T_{max.}$		5	100 3		5	100 3	pA nA
I _{ib}	Input Bias Current * $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$		30	200 7		30	200 7	pA nA
V_{icm}	Input Common Mode Voltage Range	±11.5	+15 -12		±11.5	+15 -12		V
V _{OPP}	Output Voltage Swing (R _L = $10k\Omega$) $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max}$.	20 20	27		20 20	27		V
A _{vd}	Large Signal Voltage Gain ($R_L = 10k\Omega$, $V_0 = \pm 10V$) $T_{amb} = 25^{\circ}C$ $T_{min.} \le T_{amb} \le T_{max.}$	4 4	6		4 4	6		V/mV
GBP	Gain Bandwidth Product $(T_{amb} = 25^{\circ}C, R_L = 10k\Omega, C_L = 100pF)$		1			1		MHz
Ri	Input Resistance		10 ¹²			10 ¹²		Ω
CMR	Common Mode Rejection Ratio $(R_s = 50\Omega, T_{amb} = 25^{\circ}C)$	80	86		80	86		dB
SVR	Supply Voltage Rejection Ratio $(R_s = 50\Omega, T_{amb} = 25^{\circ}C)$	80	95		80	95		dB
I _{cc}	Supply Current, no Load (T _{amb} = 25°C, no load, no signal)		200	250		200	250	μА
P _D	Total Power Consumption (T _{amb} = 25°C, no load, no signal)		6	7.5		6	7.5	mW
SR	Slew Rate (V_i = 10V, R_L = 10k Ω , C_L = 100pF, A_V = 1)	1.5	3.5		1.5	3.5		V/µs
t _r	Rise Time (V_i = 20mV, R_L = 10k Ω , C_L = 100pF, A_V = 1)		0.2			0.2		μs
Kov	Overshoot Factor (V_i = 20mV, R_L = 10k Ω , C_L = 100pF, A_V = 1) - (see figure 1)		10			10		%
e _n	Equivalent Input Noise Voltage $(R_s = 100\Omega, f = 1KHz)$		42			42		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

^{*} The input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperature as close to the ambient temperature as possible.

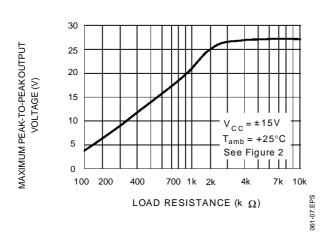
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS SUPPLY VOLTAGE

30 MAXIMUM PEAK-TO-PEAK OUTPUT R_L = 10 $k\Omega$ 25 $T_{amb} = +25^{\circ}C$ See figure 2 VOLTAGE (V) 20 15 10 5 0 10 12 16 SUPPLY VOLTAGE (V) 061-05.EPS

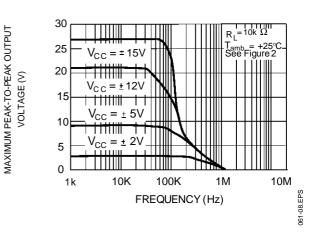
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREE AIR TEMP.



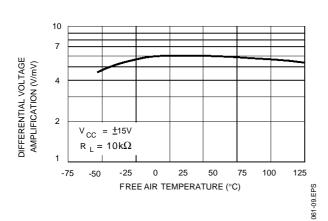
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS LOAD RESISTANCE



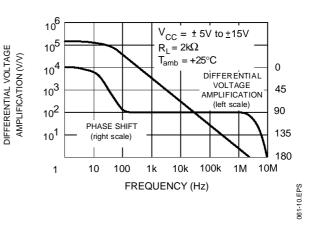
MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE VERSUS FREQUENCY



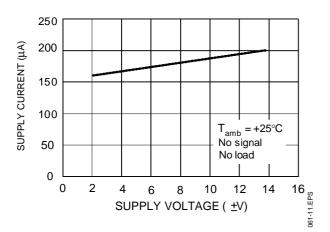
DIFFERENTIAL VOLTAGE AMPLIFICATION VERSUS FREE AIR TEMPERATURE



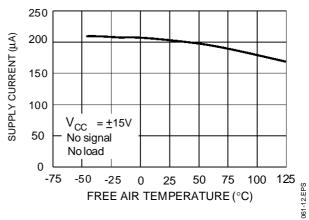
LARGE SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT VERSUS FREQUENCY



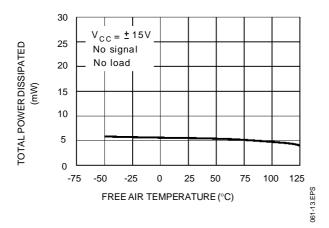
SUPPLY CURRENT PER AMPLIFIER VERSUS SUPPLY VOLTAGE



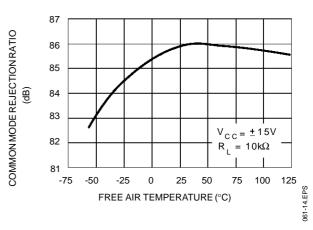
SUPPLY CURRENT PER AMPLIFIER VERSUS FREE AIR TEMPERATURE



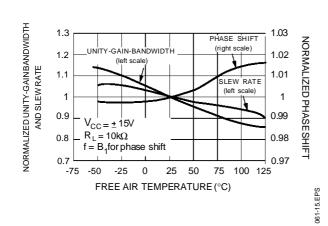
TOTAL POWER DISSIPATED VERSUS FREE AIR TEMPERATURE



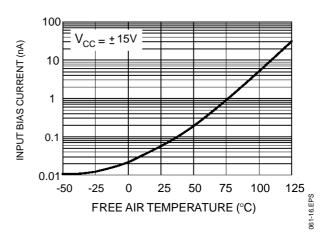
COMMON MODE REJECTION RATIO VERSUS FREE AIR TEMPERATURE



NORMALIZED UNITY GAIN BANDWIDTH SLEW RATE, AND PHASE SHIFT VERSUS TEMPERATURE

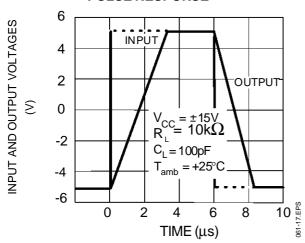


INPUT BIAS CURRENT VERSUS FREE AIR TEMPERATURE

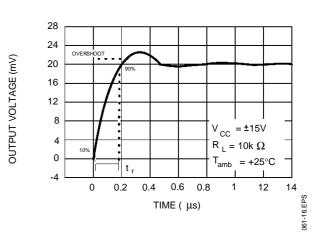


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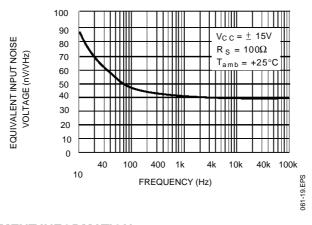
VOLTAGE FOLLOWER LARGE SIGNAL PULSE RESPONSE



OUTPUT VOLTAGE VERSUS ELAPSED TIME



EQUIVALENT INPUT NOISE VOLTAGE VERSUS FREQUENCY



PARAMETER MEASUREMENT INFORMATION

Figure 1: Voltage follower

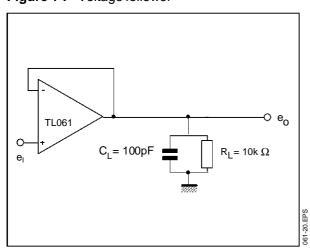
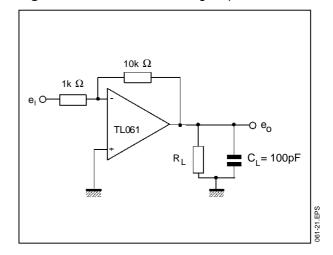
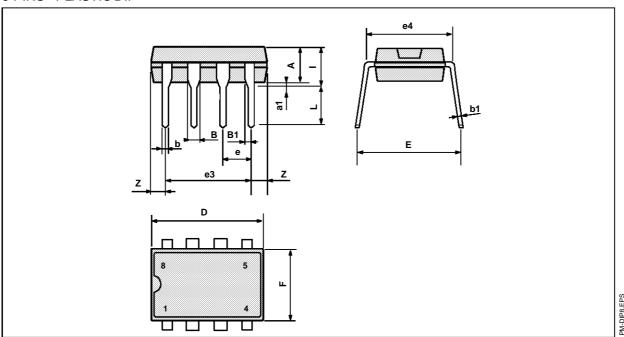


Figure 2: Gain-of-10 inverting amplifier



PACKAGE MECHANICAL DATA

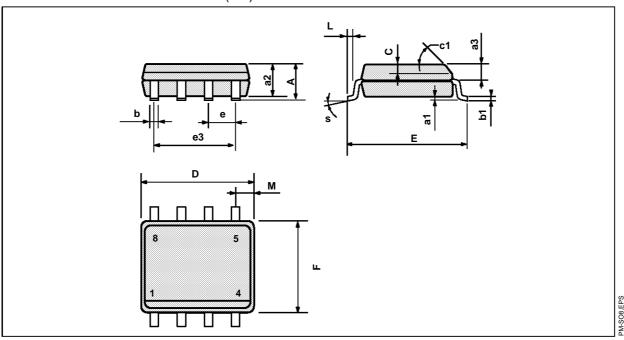
8 PINS - PLASTIC DIP



Dimensions		Millimeters		Inches			
Dimensions	Min.	Тур.	Max.	Min.	Тур.	Max.	
А		3.32			0.131		
a1	0.51			0.020			
В	1.15		1.65	0.045		0.065	
b	0.356		0.55	0.014		0.022	7
b1	0.204		0.304	0.008		0.012	
D			10.92			0.430	
Е	7.95		9.75	0.313		0.384	
е		2.54			0.100		
e3		7.62			0.300		
e4		7.62			0.300		7
F			6.6			0260	
i			5.08			0.200	
L	3.18		3.81	0.125		0.150	7
Z			1.52			0.060	- IBI BAIC

PACKAGE MECHANICAL DATA

8 PINS - PLASTIC MICROPACKAGE (SO)



Dimensions		Millimeters			Inches	
Dimensions	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
С	0.25		0.5	0.010		0.020
c1			45°	(typ.)	•	
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
М			0.6			0.024
S			8° (max.)		

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